

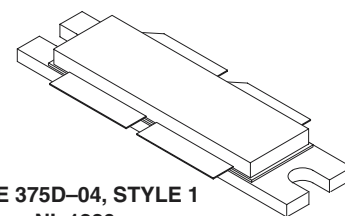
The RF Sub-Micron MOSFET Line  
**RF Power Field Effect Transistor**  
**N-Channel Enhancement-Mode Lateral MOSFET**

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for FM, TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

- W-CDMA Performance @ -45 dBc, 5 MHz Offset, 15 DTCH, 1 Perch  
Output Power — 14 Watts (Avg.)  
Power Gain — 11.5 dB  
Efficiency — 16%
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2170 MHz, 120 Watts (CW) Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters

**MRF21120**

**2170 MHz, 120 W, 28 V  
LATERAL N-CHANNEL  
RF POWER MOSFET**



**CASE 375D-04, STYLE 1  
NI-1230**

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	389 2.22	Watts W/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	200	$^\circ\text{C}$

**ESD PROTECTION CHARACTERISTICS**

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.45	$^\circ\text{C}/\text{W}$

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS (1)</b>					
Drain–Source Breakdown Voltage ( $V_{GS} = 0 \text{ Vdc}$ , $I_D = 20 \mu\text{Adc}$ )	$V_{(BR)DSS}$	65	—	—	Vdc
Gate–Source Leakage Current ( $V_{GS} = 5 \text{ Vdc}$ , $V_{DS} = 0 \text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28 \text{ Vdc}$ , $V_{GS} = 0 \text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
<b>ON CHARACTERISTICS (1)</b>					
Forward Transconductance ( $V_{DS} = 10 \text{ Vdc}$ , $I_D = 2 \text{ Adc}$ )	$g_{fs}$	—	4.8	—	S
Gate Threshold Voltage ( $V_{DS} = 10 \text{ V}$ , $I_D = 200 \mu\text{A}$ )	$V_{GS(th)}$	2.5	3	3.8	Vdc
Gate Quiescent Voltage ( $V_{DS} = 28 \text{ V}$ , $I_D = 500 \text{ mA}$ )	$V_{GS(Q)}$	3	3.9	5	Vdc
Drain–Source On–Voltage ( $V_{GS} = 10 \text{ V}$ , $I_D = 2 \text{ A}$ )	$V_{DS(on)}$	—	0.38	0.5	Vdc
<b>DYNAMIC CHARACTERISTICS (1)</b>					
Reverse Transfer Capacitance ( $V_{DS} = 28 \text{ Vdc}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$ )	$C_{rss}$	—	2.8	—	pF
<b>FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system) (2)</b>					
Common–Source Amplifier Power Gain ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2170.0 \text{ MHz}$ , $f_2 = 2170.1 \text{ MHz}$ )	$G_{ps}$	10.5	11.4	—	dB
Drain Efficiency ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2170.0 \text{ MHz}$ , $f_2 = 2170.1 \text{ MHz}$ )	$\eta$	30	34.5	—	%
Intermodulation Distortion ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2170.0 \text{ MHz}$ , $f_2 = 2170.1 \text{ MHz}$ )	IMD	—	–31	–28	dB
Input Return Loss ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2170.0 \text{ MHz}$ , $f_2 = 2170.1 \text{ MHz}$ )	IRL	—	–12	–9	dB
Common–Source Amplifier Power Gain ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2140.0 \text{ MHz}$ , $f_2 = 2140.1 \text{ MHz}$ )	$G_{ps}$	—	11.5	—	dB
Common–Source Amplifier Power Gain ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2110.0 \text{ MHz}$ , $f_2 = 2110.1 \text{ MHz}$ )	$G_{ps}$	—	11.5	—	dB
Drain Efficiency ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2110.0 \text{ MHz}$ , $f_2 = 2110.1 \text{ MHz}$ )	$\eta$	—	34.5	—	%
Intermodulation Distortion ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2110.0 \text{ MHz}$ , $f_2 = 2110.1 \text{ MHz}$ )	IMD	—	–31	—	dB
Input Return Loss ( $V_{DD} = 28 \text{ Vdc}$ , $P_{out} = 120 \text{ W PEP}$ , $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2110.0 \text{ MHz}$ , $f_2 = 2110.1 \text{ MHz}$ )	IRL	—	–12	—	dB
Power Output, 1 dB Compression Point ( $V_{DD} = 28 \text{ Vdc}$ , CW, $I_{DQ} = 2 \times 500 \text{ mA}$ , $f_1 = 2170.0 \text{ MHz}$ )	P1dB	—	120	—	Watts

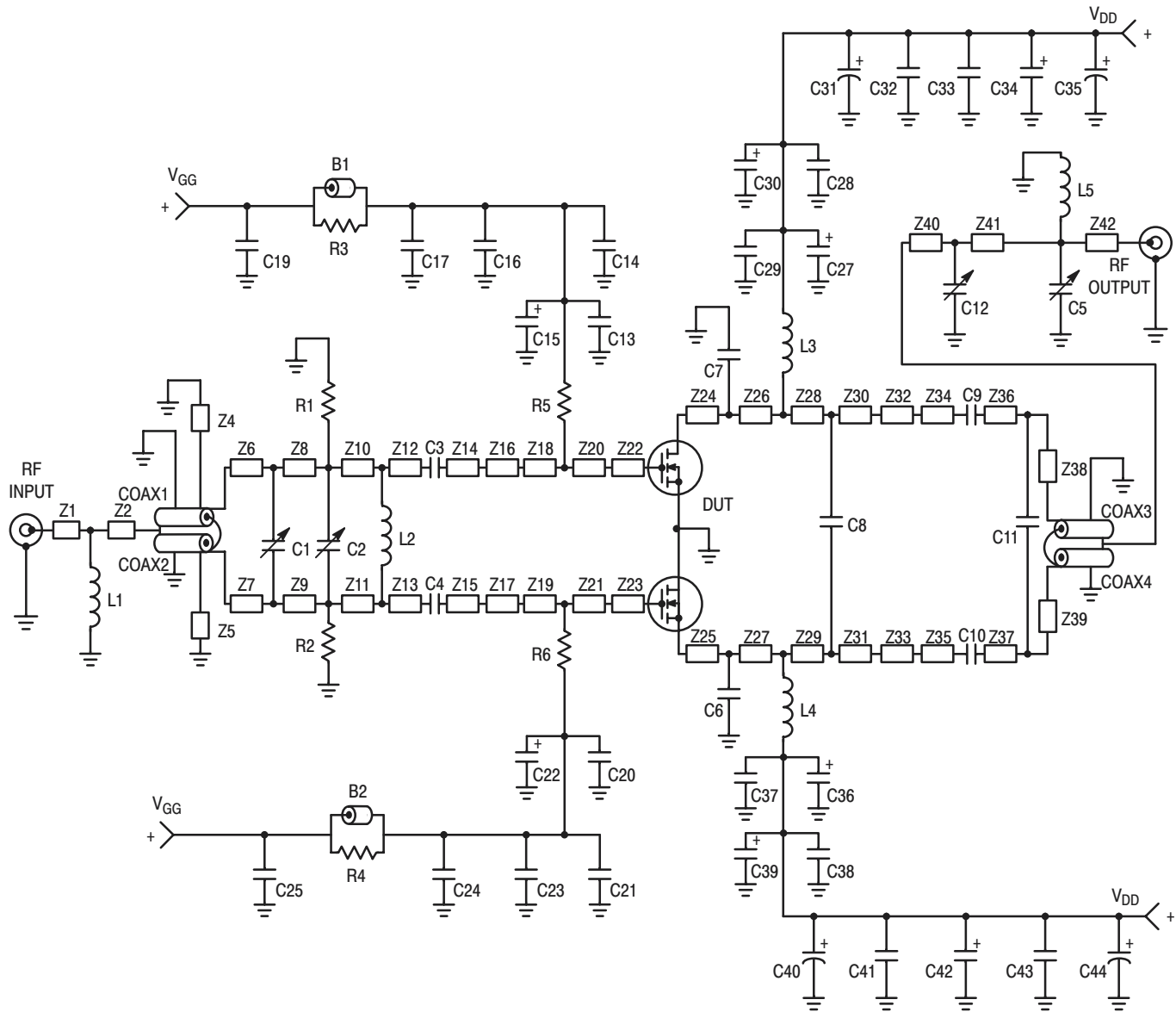
(1) Each side of device measured separately.

(2) Device measured in push–pull configuration.

**ELECTRICAL CHARACTERISTICS — continued** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>FUNCTIONAL TESTS</b> (In Motorola Test Fixture, 50 ohm system) (2) (continued)					
Common–Source Amplifier Power Gain ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 120\text{ W CW}$ , $I_{DQ} = 2 \times 500\text{ mA}$ , $f_1 = 2170.0\text{ MHz}$ )	$G_{ps}$	—	10.5	—	dB
Drain Efficiency ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 120\text{ W CW}$ , $I_{DQ} = 2 \times 500\text{ mA}$ , $f_1 = 2170.0\text{ MHz}$ )	$\eta$	—	42	—	%
Output Mismatch Stress ( $V_{DD} = 28\text{ Vdc}$ , $P_{out} = 120\text{ W CW}$ , $I_{DQ} = 2 \times 500\text{ mA}$ , $f = 2.17\text{ GHz}$ , $VSWR = 10:1$ , All Phase Angles at Frequency of Tests)	$\Psi$	No Degradation In Output Power Before and After Test			

(2) Device measured in push–pull configuration.



B1, B2	Ferrite Beads, Fair Rite	Z2	0.320" x 0.080" Microstrip
C1, C2, C12	0.6 – 4.5 pF Variable Capacitors, Johanson Gigatrim	Z4, Z5	1.050" x 0.080" Microstrip
C3, C4, C9, C10	10 pF Chip Capacitors, B Case, ATC	Z6, Z7	0.120" x 0.080" Microstrip
C5	0.4 – 2.5 pF Variable Capacitor, Johanson Gigatrim	Z8, Z9	0.140" x 0.080" Microstrip
C6, C7	2.0 pF Chip Capacitors, B Case, ATC	Z10, Z11	0.610" x 0.080" Microstrip
C8	0.5 pF Chip Capacitor, B Case, ATC	Z12, Z13	0.135" x 0.080" Microstrip
C11	0.2 pF Chip Capacitor, B Case, ATC	Z14, Z15	0.130" x 0.080" Microstrip
C13, C20, C29, C37	5.1 pF Chip Capacitors, B Case, ATC	Z16, Z17	0.300" x 0.350" Microstrip
C14, C21, C28, C38	91 pF Chip Capacitors, B Case, ATC	Z18, Z19	0.150" x 0.500" Microstrip
C15, C22, C27, C34, C36, C42	22 $\mu$ F, 35 V Tantalum Surface Mount Chip Capacitors, Kemet	Z20, Z21	0.075" x 0.500" Microstrip
C16, C23, C33, C43	0.039 $\mu$ F Chip Capacitors, B Case, ATC	Z22, Z23	0.330" x 0.500" Microstrip
C17, C24, C32, C41	1000 pF Chip Capacitors, B Case, ATC	Z24, Z25	0.100" x 0.550" Microstrip
C19, C25	0.022 $\mu$ F Chip Capacitors, B Case, ATC	Z26, Z27	0.175" x 0.550" Microstrip
C30, C39	1.0 $\mu$ F, 35 V Tantalum Surface Mount Chip Capacitors, Kemet	Z28, Z29	0.045" x 0.550" Microstrip
C31, C40	100 $\mu$ F, 50 V Electrolytic Capacitors, Sprague	Z30, Z31	0.190" x 0.325" Microstrip
C35, C44	470 $\mu$ F, 63 V Electrolytic Capacitors, Sprague	Z32, Z33	0.080" x 0.325" Microstrip
Coax1, Coax2	25 $\Omega$ Semi Rigid Coax, 70 mil OD, 1.05" Long	Z34, Z35	0.515" x 0.080" Microstrip
Coax3, Coax4	50 $\Omega$ Semi Rigid Coax, 85 mil OD, 1.05" Long	Z36, Z37	0.020" x 0.080" Microstrip
L1, L5	5.0 nH Minispring Inductors, Coilcraft	Z38, Z39	0.565" x 0.080" Microstrip
L2	8.0 nH Minispring Inductor, Coilcraft	Z40	0.100" x 0.080" Microstrip
L3, L4	7.15 nH Minispring Inductors, Coilcraft	Z41	0.470" x 0.080" Microstrip
R1, R2	1 k $\Omega$ , 1/4 W Fixed Metal Film Resistors, Dale	Z42	0.100" x 0.080" Microstrip
R3, R4	270 $\Omega$ , 1/8 W Fixed Film Chip Resistors, Dale	Board Material	0.03" Teflon <sup>®</sup> , $\epsilon_r = 2.55$ Copper Clad, 2 oz. Cu
R5, R6	1.2 k $\Omega$ , 1/8 W Fixed Film Chip Resistors, Dale	Connectors	N-Type Panel Mount, Stripline
Z1	0.150" x 0.080" Microstrip		

Figure 1. 2.1 – 2.2 GHz Broadband Test Circuit Schematic

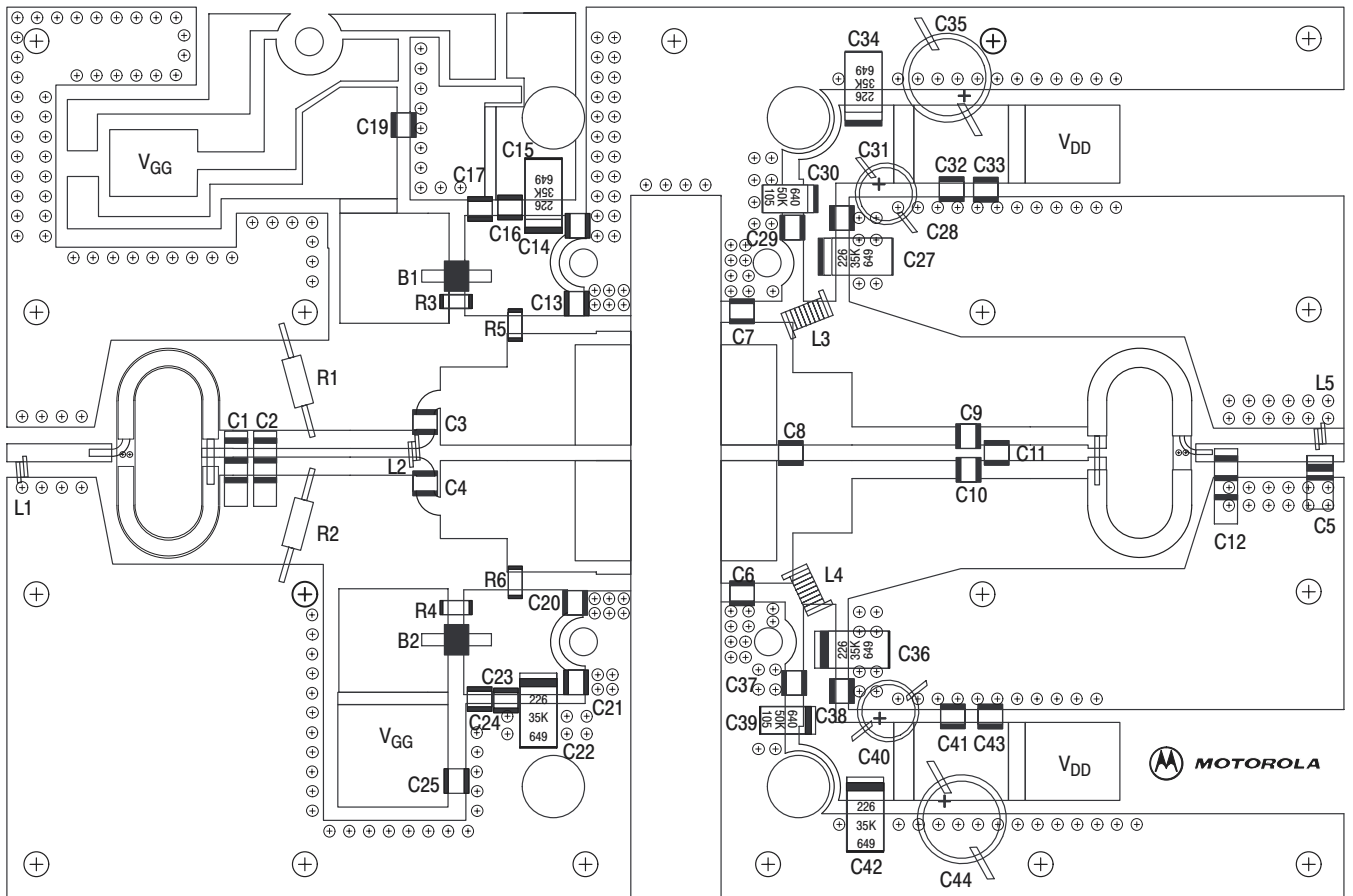
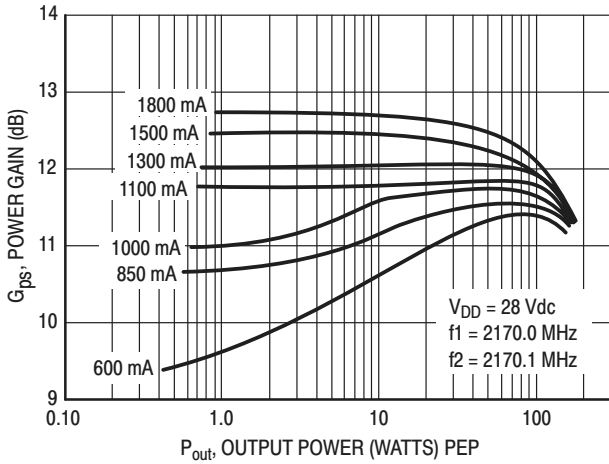
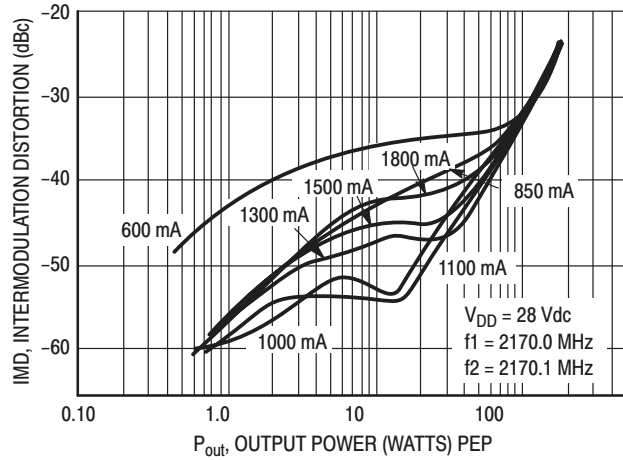


Figure 2. 2.1 – 2.2 GHz Broadband Test Circuit Component Layout

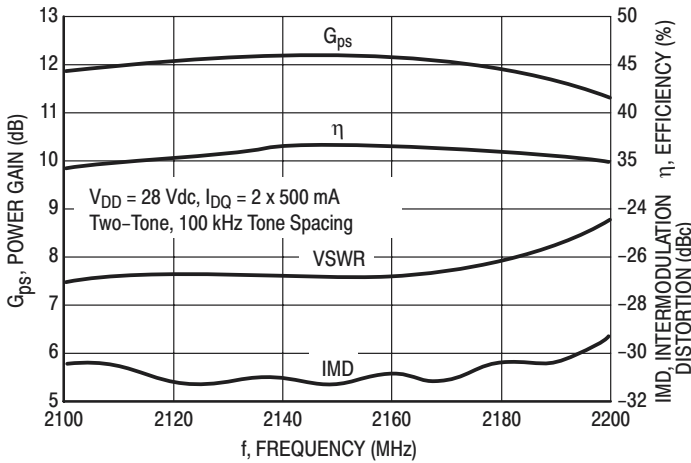
## TYPICAL CHARACTERISTICS



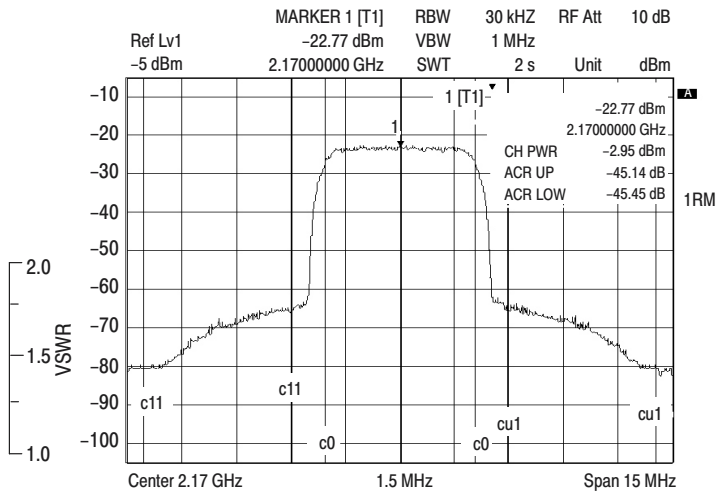
**Figure 3. Power Gain versus Output Power**



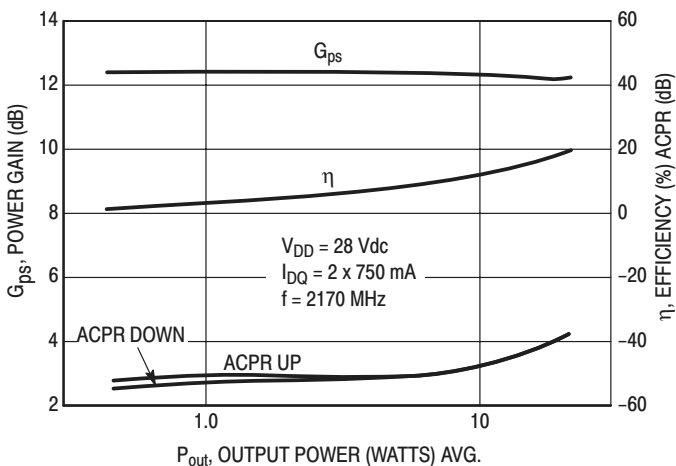
**Figure 4. Intermodulation Distortion versus Output Power**



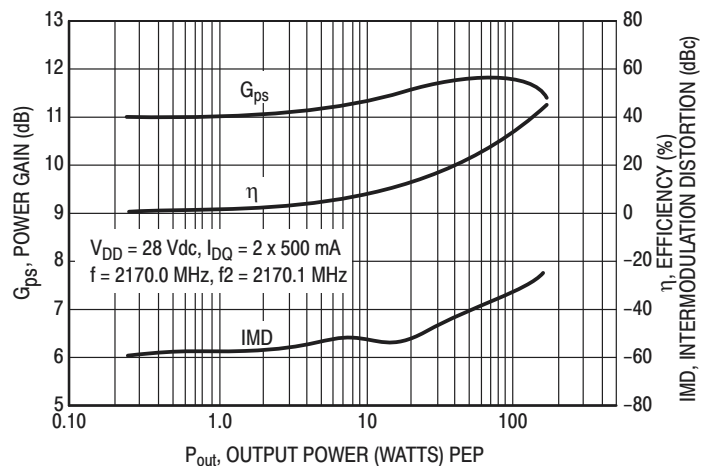
**Figure 5. Class AB Broadband Circuit Performance**



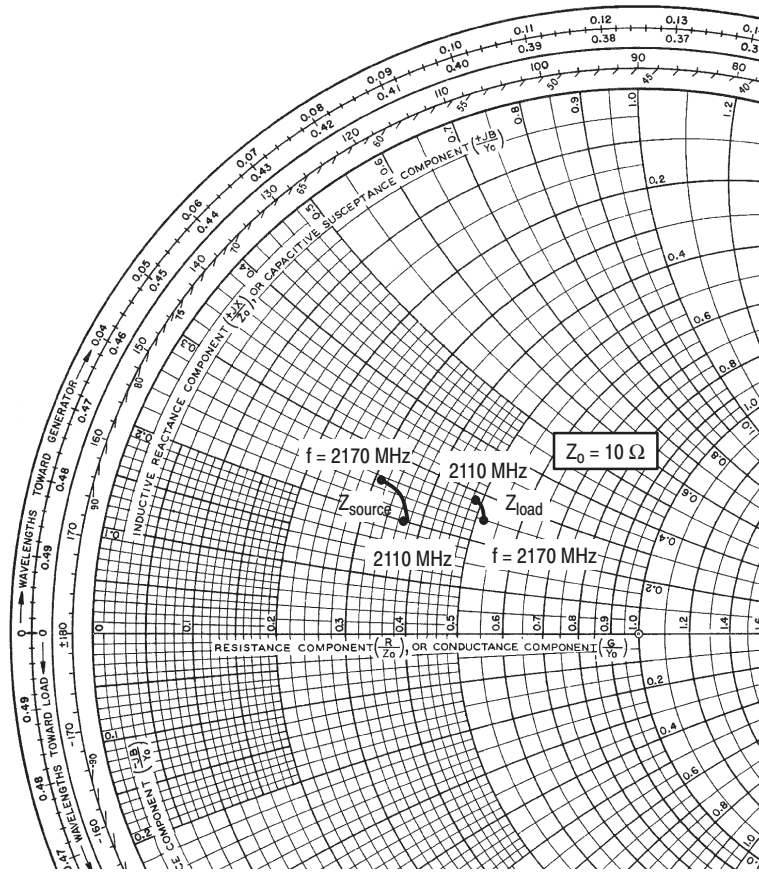
**Figure 6. 2.17 GHz W-CDMA Mask at 14 Watts (Avg.), 5 MHz Offset, 15 DTCH, 1 Perch**



**Figure 7. Power Gain, Efficiency, ACPR versus Output Power (W-CDMA)**



**Figure 8. Power Gain, Efficiency, IMD versus Output Power**



$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 2 \times 500\text{ mA}$ ,  $P_{out} = 120\text{ W PEP}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
2110	$3.7 + j2.0$	$4.9 + j2.8$
2140	$3.5 + j2.4$	$5.1 + j2.7$
2170	$3.1 + j2.5$	$5.2 + j2.5$

$Z_{source}$  = Test circuit impedance as measured from gate to gate, balanced configuration.

$Z_{load}$  = Test circuit impedance as measured from drain to drain, balanced configuration.

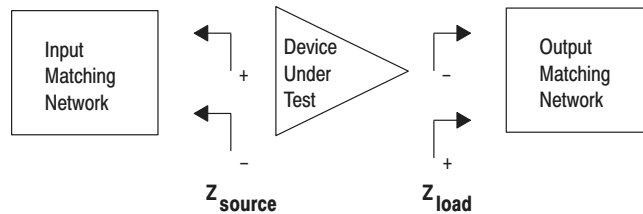
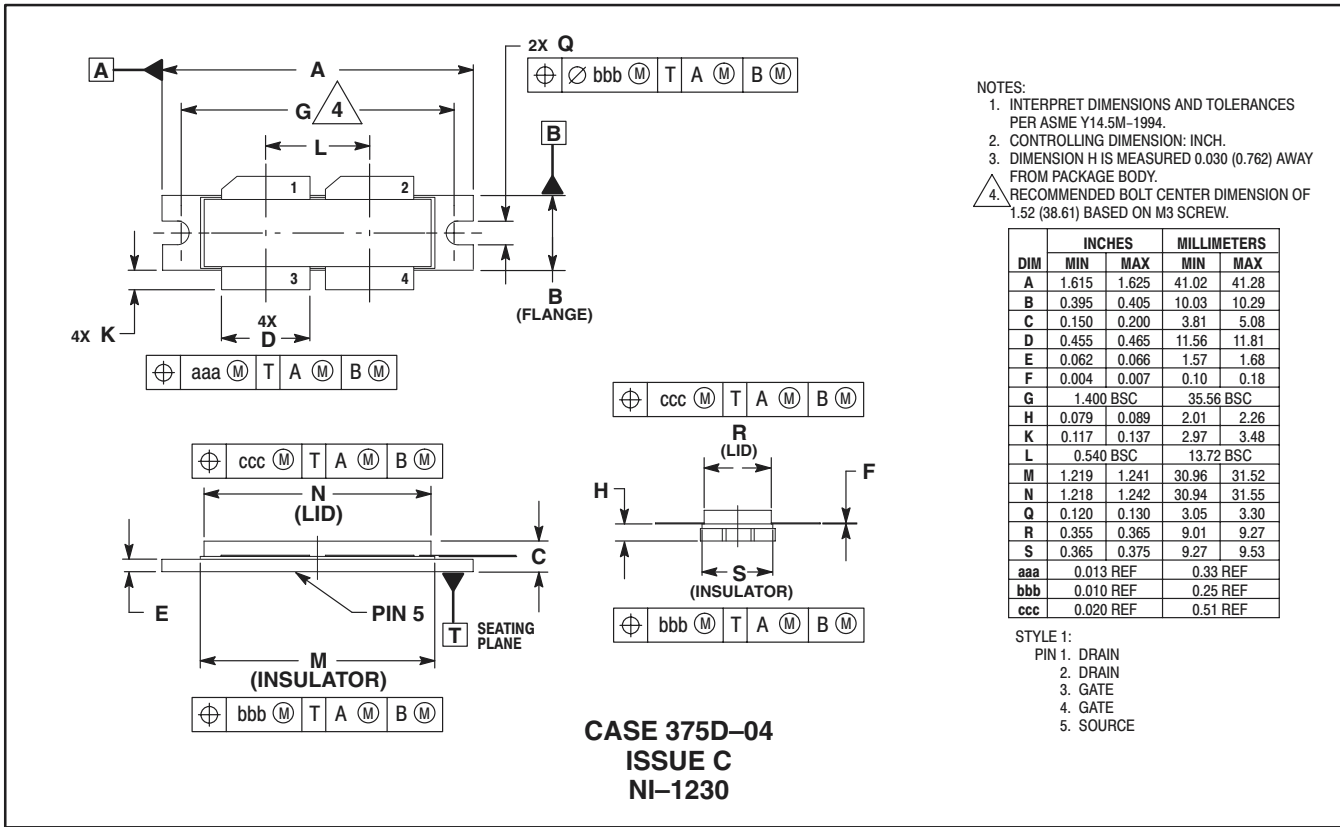



Figure 9. Series Equivalent Input and Output Impedance

## PACKAGE DIMENSIONS



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